



NTR1P02T3G Information



For Reference Only

Part Number NTR1P02T3G

Manufacturer ON Semiconductor

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

DescriptionMOSFET P-CH 20V 1A SOT-23**Package**TO-236-3, SC-59, SOT-23-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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Certified Quality

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NTR1P02T3G Specifications

Manufacturer Part Number NTR I PO2T3 G Manufacturer ON Semiconductor Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-236-3, SC-59, SOT-23-3 Series - FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 20V Current - Continuous Drain (Id) @ 25°C 1A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.3V @ 250μA Gate Charge (Qg) (Max) @ Vgs 2.5nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 165pF @ 5V Vgs (Max) ± 20V FET Feature - Power Dissipation (Max) 400mW (Ta) Rds On (Max) @ Id, Vgs 180 mOhm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-23-3 (TO-236) Package / Case TO-236-3, SC-59, SOT-23-3 Report errors?		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-236-3, SC-59, SOT-23-3 Series - FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 20V Current - Continuous Drain (Id) @ 25°C 1A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.3V @ 250μA Gate Charge (Qg) (Max) @ Vgs 2.5nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 165pF @ 5V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 400mW (Ta) Rds On (Max) @ Id, Vgs 180 mOhm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-23-3 (TO-236) Package / Case TO-236-3, SC-59, SOT-23-3	Manufacturer Part Number	NTR1P02T3G
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Package TO-236-3, SC-59, SOT-23-3 Series - FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 20V Current - Continuous Drain (Id) @ 25°C 1A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.3V @ 250μA Gate Charge (Qg) (Max) @ Vgs 2.5nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 165pF @ 5V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 400mW (Ta) Rds On (Max) @ Id, Vgs 180 mOhm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-23-3 (TO-236) Package / Case TO-236-3, SC-59, SOT-23-3	Category	Discrete Semiconductor Products
Series - FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 20V Current - Continuous Drain (Id) @ 25°C 1A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.3V @ 250μA Gate Charge (Qg) (Max) @ Vgs 2.5nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 165pF @ 5V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 400mW (Ta) Rds On (Max) @ Id, Vgs 180 mOhm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-23-3 (TO-236) Package / Case TO-236-3, SC-59, SOT-23-3		Transistors - FETs, MOSFETs - Single
FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 20V Current - Continuous Drain (Id) @ 25°C 1A (Ta) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 2.3V @ 250μA Gate Charge (Qg) (Max) @ Vgs 165pF @ 5V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 180 mOhm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case TO-236-3, SC-59, SOT-23-3	Package	TO-236-3, SC-59, SOT-23-3
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)20VCurrent - Continuous Drain (Id) @ 25°C1A (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.3V @ 250μAGate Charge (Qg) (Max) @ Vgs2.5nC @ 5VInput Capacitance (Ciss) (Max) @ Vds165pF @ 5VVgs (Max)±20VFET Feature-Power Dissipation (Max)400mW (Ta)Rds On (Max) @ Id, Vgs180 mOhm @ 1.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-23-3 (TO-236)Package / CaseTO-236-3, SC-59, SOT-23-3	Series	-
Drain to Source Voltage (Vdss)20VCurrent - Continuous Drain (Id) @ 25°C1A (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.3V @ 250μAGate Charge (Qg) (Max) @ Vgs2.5nC @ 5VInput Capacitance (Ciss) (Max) @ Vds165pF @ 5VVgs (Max)±20VFET Feature-Power Dissipation (Max)400mW (Ta)Rds On (Max) @ Id, Vgs180 mOhm @ 1.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-23-3 (TO-236)Package / CaseTO-236-3, SC-59, SOT-23-3	FET Type	P-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 180 mOhm @ 1.5A, 10V Operating Temperature Supplier Device Package Package / Case 1A (Ta)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 180 mOhm @ 1.5A, 10V Operating Temperature Surplier Device Package Package / Case 4.5V, 10V 2.3V @ 250μA 2.5nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 165pF @ 5V ±20V FET Feature - Surface Mount Surface Mount Surface Mount TO-236-3, SC-59, SOT-23-3	Drain to Source Voltage (Vdss)	20V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Input Capacitance (Tiss) (Max) Bundle English (Tiss) Surface Mount Supplier Device Package Package / Case 2.3V @ 250μA 2.5nC @ 5V 165pF @ 5V ±20V FET Feature - Nome of the properties of the propertie	Current - Continuous Drain (Id) @ 25°C	1A (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) +20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 180 mOhm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case TO-236-3, SC-59, SOT-23-3	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) E20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 180 mOhm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-23-3 (TO-236) Package / Case TO-236-3, SC-59, SOT-23-3	Vgs(th) (Max) @ Id	2.3V @ 250μA
Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 400mW (Ta) Rds On (Max) @ Id, Vgs 180 mOhm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-23-3 (TO-236) Package / Case TO-236-3, SC-59, SOT-23-3	Gate Charge (Qg) (Max) @ Vgs	2.5nC @ 5V
FET Feature - Power Dissipation (Max) 400mW (Ta) Rds On (Max) @ Id, Vgs 180 mOhm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-23-3 (TO-236) Package / Case TO-236-3, SC-59, SOT-23-3	Input Capacitance (Ciss) (Max) @ Vds	165pF @ 5V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 180 mOhm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-23-3 (TO-236) Package / Case TO-236-3, SC-59, SOT-23-3	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs180 mOhm @ 1.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-23-3 (TO-236)Package / CaseTO-236-3, SC-59, SOT-23-3	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-23-3 (TO-236) Package / Case TO-236-3, SC-59, SOT-23-3	Power Dissipation (Max)	400mW (Ta)
Mounting Type Surface Mount Supplier Device Package SOT-23-3 (TO-236) Package / Case TO-236-3, SC-59, SOT-23-3	Rds On (Max) @ Id, Vgs	180 mOhm @ 1.5A, 10V
Supplier Device Package SOT-23-3 (TO-236) Package / Case TO-236-3, SC-59, SOT-23-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-236-3, SC-59, SOT-23-3	Mounting Type	Surface Mount
	Supplier Device Package	SOT-23-3 (TO-236)
Report errors?	Package / Case	TO-236-3, SC-59, SOT-23-3
		Report errors?

NTR1P02T3G Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

NTR1P02T3G Payment Methods



















NTR1P02T3G Shipping Methods













If you have any question about NTR1P02T3G, please do not hesitate to contact us!

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